

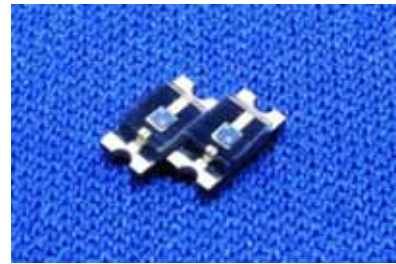
Silicon PIN Photo Diodes

Model No. PPD-108

Optoelectronic device

Features

- Small & Compact SMD type
- Capable 3-way soldering: front, rear and side plain
- Easy positioning with 2.6x3.2 rectangular hole
- High sensitivity & reliability



Absolute Maximum Ratings

Ta = 25

Parameter	Symbol	Value	Unit
DC Reverse Voltage	V_R	20	V
Operating Temperature	Topr	-20 ~ +60	
Storage Temperature	Tstg	-30 ~ +80	

Electro-optical Characteristics

Ta = 25

Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
Sensitive Range		320		1150	nm	Equivalent energy
Peak sensitive wavelength	λ_p		880		nm	Equivalent energy
Short Circuit Current	Isc	100	150	200	nA	100Lx, 2856 ° K
Dark current	Id	10			pA	$V_R=1V$. RH 65%
Shortcircuit current temp. coefficient	τ		0.2	0.3	%/	100Lx, 2856 ° K
Dark current temp. coefficient	τ		4	5	Times/10	$V_R=1V$. RH 65%
Terminal capacitance	C_T		20		pF	$V_R=0V$, f=1MHz

External Dimension (unit: mm)

